

L Number	Hits	Search Text	DB	Time stamp
3	2	annealing with (substrate or wafer) with insulation with (second adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:35
4	2	annealing same (substrate or wafer) same insulation same (second adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:34
5	858	(anneal\$4 or (heat adj treatment)) same sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:37
6	1	(anneal\$4 or (heat adj treatment)) same sublim\$5 same (insulation adj film)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:50
7	66	(insulation adj film) with ((first or upper) adj side) with ((second or bottom) adj side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:52
9	0	((insulation adj film) with ((first or upper) adj side) with ((second or bottom) adj side)) and (etch\$4 with (first or upper))) and anneal\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:54
8	47	((insulation adj film) with ((first or upper) adj side) with ((second or bottom) adj side)) and (etch\$4 with (first or upper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 11:57
10	35	sublimation with ((second or bottom) near3 substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 12:05
11	781	sublimation and 438.clas.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:00
12	729	(sublimation and 438.clas.) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 12:57
13	199	(sublimation with (substrate or wafer)) and 438.clas.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:01
16	781	sublimation and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:01

17	199	(sublimation with (substrate or wafer)) and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:18
18	15	(sublimation with (substrate or wafer)) same insul\$5 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/27 13:19